

Band Switching Diode

- **Applications**

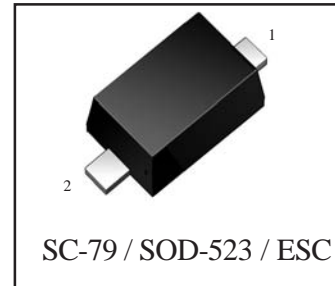
High frequency switching

- **Features**

- 1) Small surface mounting type.
- 2) High reliability.
- 3) We declare that the material of product compliance with RoHS requirements.

- **Construction**

Silicon epitaxial planar



Driver Marking

FDS114E = 1

Absolute maximum ratings ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	35	V
DC forward current	I_F	100	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~+125	$^\circ\text{C}$

Electrical characteristics ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	1.0	V	$I_F=10\text{mA}$
Reverse current	I_R	–	–	50	nA	$V_R=25\text{V}$
Capacitance between terminals	C_T	–	–	1.2	pF	$V_R=6\text{V}$, $f=1\text{MHz}$
Forward operating resistance	r_F	–	–	0.9	Ω	$I_F=2\text{mA}$, $f=100\text{MHz}$

Ordering Information

Device	Marking	Shipping
LBA277T1G	1	3000/Tape&Reel
LBA277T3G	1	10000/Tape&Reel

Electrical characteristic curves ($T_A=25^\circ\text{C}$)

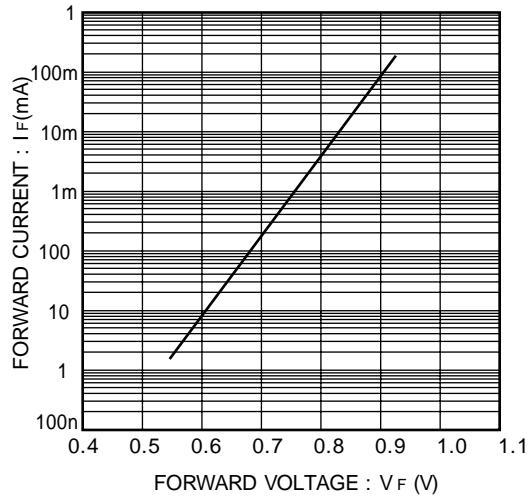


Fig. 1 Forward characteristics

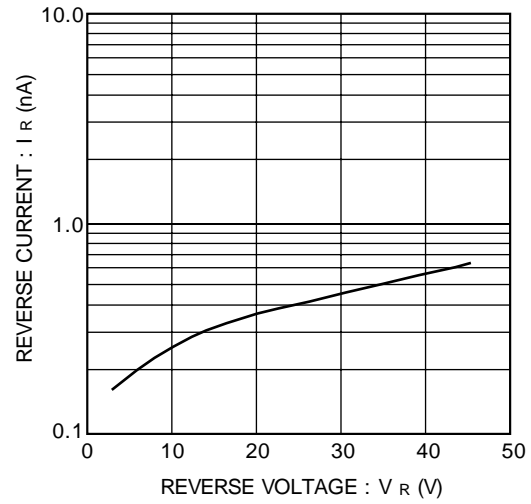


Fig. 2 Reverse characteristics

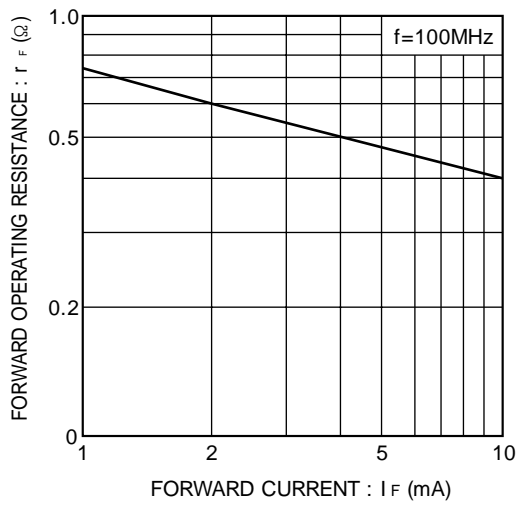


Fig. 4 Forward operating resistance characteristics

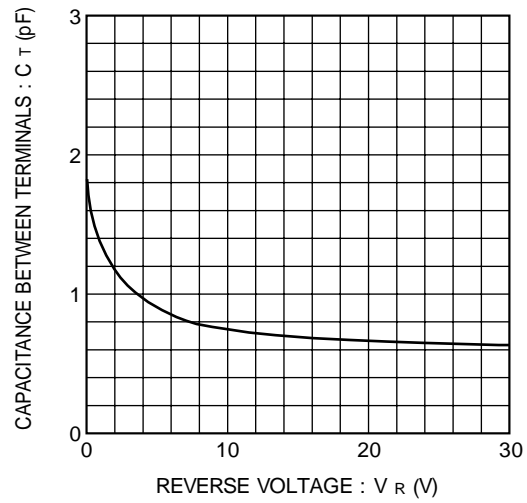
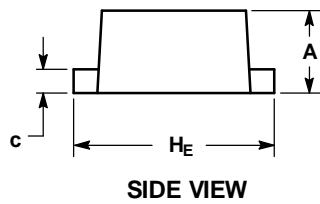
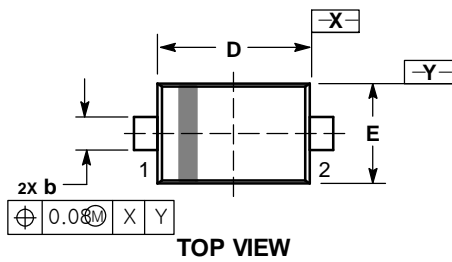
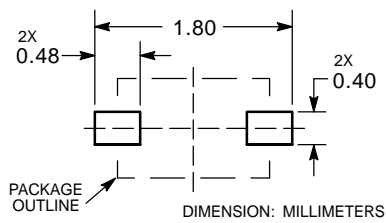


Fig. 3 Capacitance between terminals characteristics

SOD-523



RECOMMENDED SOLDERING FOOTPRINT*



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.50	0.60	0.70
b	0.25	0.30	0.35
c	0.07	0.14	0.20
D	1.10	1.20	1.30
E	0.70	0.80	0.90
H _E	1.50	1.60	1.70
L	0.30 REF		
L2	0.15	0.20	0.25